RECTRON
SEMICONDUCTOR
TECHNICAL SPECIFICATION

DAN217U

SOT-323 SWITCHING DIODE

FEATURES

* Power dissipation
  P_D: 200   mW (Tamb=25°C)
* Forward current
  I_F: 100   mA
* Reverse voltage
  V_R: 80   V
* Operating and storage junction temperature range
  T_J,T_{stg}: -65°C to +150°C

MECHANICAL DATA
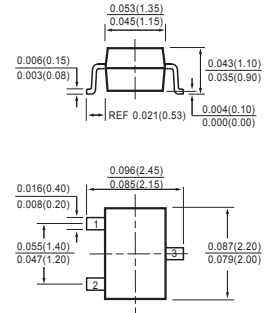
* Case: Molded plastic
* Epoxy: UL 94V-O rate flame retardant
* Lead: MIL-STD-202E method 208C guaranteed
* Mounting position: Any
* Weight: 0.006 gram
* Marking: A7

SOT-323

Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

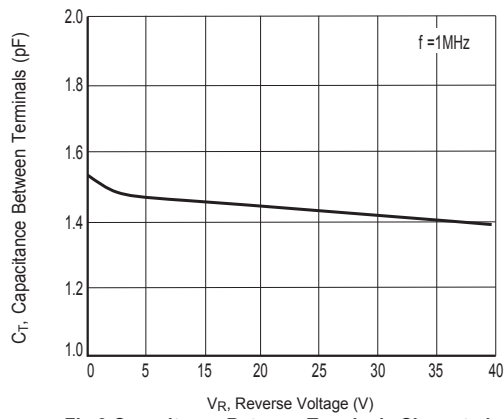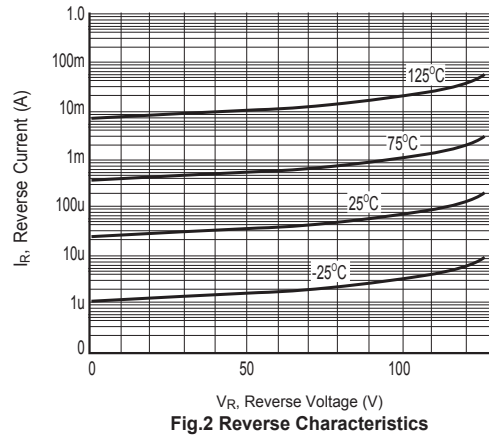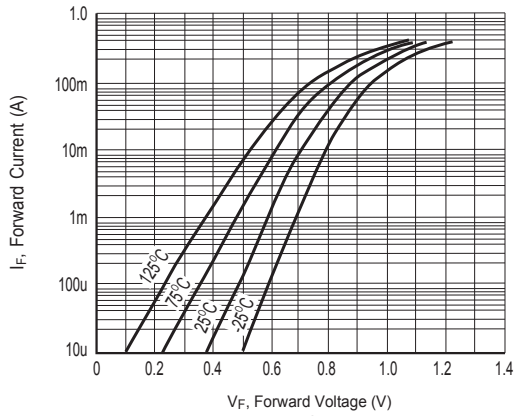Ratings at 25 ^{o}C ambient temperature unless otherwise specified.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS, SINGLE DIODE (@ T_A = 25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMITS	UNITS
Peak Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	V
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (1uS) (10mS)	I_{FSM}	400 1000	mA
Power dissipation	P_D	200	mW
Junction Temperature	T_J	150	^{o}C
Storage Temperature	T_{STG}	-55 to +150	^{o}C
Operating Temperature Range	T_{OPR}	-40 to +100	^{o}C

ELECTRICAL CHARACTERISTICS (@ T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Reverse Breakdown Voltage (I_R=100uA)	$V_{(BR)}$	80	-	-	V
Reverse voltage leakage current (V_R=70V)	I_R	-	-	0.2	uA
Forward voltage (I_F=100mA)	V_F	-	-	1200	mV

Note :   "Fully RoHS Compliant", "100% Sn plating (Pb-free)".

RATING AND CHARACTERISTICS CURVES (DAN217U)

Fig.1 Forward Characteristics

Fig.2 Reverse Characteristics

Fig.3 Capacitance Between Terminals Characterical

RECTRON

DISCLAIMER NOTICE

RECTRON